



Cite this: *RSC Adv.*, 2017, 7, 20084

# Ligand-free rutile and anatase TiO<sub>2</sub> nanocrystals as electron extraction layers for high performance inverted polymer solar cells†

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Ligand-free rutile and anatase TiO<sub>2</sub> nanocrystals have been synthesized through a hydrolytic sol–gel reaction. The morphology, crystal structure, elemental composition and band structure of the obtained nanocrystals are characterized by transmission electron microscopy, X-ray diffraction, X-ray photoelectron spectroscopy, ultraviolet photoelectron spectroscopy and UV-visible absorption spectroscopy. These two kinds of nanocrystals could serve as electron extraction layers for improving the performance in inverted polymer solar cells. Compared with the device fabricated by using amorphous TiO<sub>2</sub> (6.11%) and rutile TiO<sub>2</sub> (6.93%), the device based on anatase TiO<sub>2</sub> shows a significant enhancement in power conversion efficiency (7.85%). Meanwhile, the ideal current–voltage model for a single heterojunction solar cell is applied to clarify the junction property of the cell. The model demonstrates that the device based on anatase TiO<sub>2</sub> has effective electron extraction and hole-blocking properties.

Received 4th January 2017

Accepted 16th March 2017

DOI: 10.1039/c7ra00134g

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## 1. Introduction

Organic solar cells (OSCs) have attracted extensive attention due to their advantages such as low cost, flexibility, light weight and simple fabrication.<sup>1–4</sup> Rapid progress has led to high power conversion efficiencies (PCE) of over 10% being achieved in single-junction OSCs.<sup>5,6</sup> Meanwhile, the stability, especially in an air atmosphere, becomes a key issue for their application.<sup>7</sup> Compared with a conventional structure, inverted organic solar cells (i-OSCs) could improve the stability because of the application of high work-function metals (Ag, Au) as the anode.<sup>8–12</sup> Moreover, to achieve the inverted configuration, the indium tin oxide (ITO) cathode is modified by electron extraction materials, including metal oxides (ZnO, TiO<sub>2</sub>),<sup>13</sup> metal salts (CsF, Cs<sub>2</sub>CO<sub>3</sub>, C<sub>17</sub>H<sub>35</sub>COOCs),<sup>14–16</sup> and polyelectrolytes (PFN, PEI, PEIE).<sup>17,18</sup> Among these interfacial materials, TiO<sub>2</sub> attracts more attention due to its high chemical and thermal stability, hole blocking, and electron selectivity.<sup>19</sup>

TiO<sub>2</sub> can exist in one of three major bulk crystalline forms, rutile, anatase, and brookite; all of which can be described in terms of distorted TiO<sub>6</sub> octahedra with different symmetries or arrangements.<sup>20</sup> Among its three polymorphs, the brookite structure is not experimentally investigated as much as the others because brookite is a metastable phase with a complicated and

low-symmetry structure; furthermore, the formation of brookite TiO<sub>2</sub> is almost always accompanied by the presence of secondary phases such as anatase and/or rutile. In comparison, rutile and anatase are the two most dominant polymorphs used in applications. Usually, anatase TiO<sub>2</sub> shows a higher photocatalytic activity due to its wider band gap than rutile TiO<sub>2</sub>.<sup>21</sup>

The basic synthetic routes of TiO<sub>2</sub> nanomaterials and films have been reviewed by Chen and Sang,<sup>20,22</sup> including sol–gel, micelle, hydrothermal, solvothermal, sonochemical and microwave methods. Among these methods, the sol–gel method is a versatile route to fabricate amorphous or low crystalline TiO<sub>2</sub> nanomaterials or films at low temperature. However, the solar cells based on amorphous or low crystalline TiO<sub>2</sub> result in relatively low electron mobility and subsequently poor device performance.<sup>23</sup> Therefore, a sol–gel method combined with heat treatment was developed yielding advances for DSSCs. For example, Agarwala reported a series of methods to prepare TiO<sub>2</sub> films with high crystallinity and stable mesoporous structure, and improved performance of the DSSCs was achieved.<sup>24–27</sup>

To obtain the crystalline TiO<sub>2</sub> nanomaterials or films with tunable crystal phases, one common method is annealing the spin-coated titanium precursors in different ranges of temperature. For example, anatase TiO<sub>2</sub> films can be obtained by annealing titanium isopropoxide at 400–500 °C.<sup>28</sup> Upon increasing the annealing temperature to 600 °C, phase transformation occurs and rutile TiO<sub>2</sub> films could be obtained.<sup>29</sup> These strategies above were well-developed in DSSCs. But in the case of OSCs, the electron extraction layer (EEL) requires a thin (usually below 50 nm) and condensed TiO<sub>2</sub> film for high electron mobility and high transmittance. The high-temperature calcination will cause large

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† Electronic supplementary information (ESI) available. See DOI: 10.1039/c7ra00134g



grain or particle size for the crystalline TiO<sub>2</sub>. Meanwhile, the metal atoms (Ti, In, Sn) from ITO will diffuse into TiO<sub>2</sub> films during the calcination process, resulting in altered optical and electronic properties.<sup>30</sup> Therefore, the fabrication of the crystalline TiO<sub>2</sub> thin films at low temperature is required. With the development of the synthesis, the controllable size, phase and morphology of TiO<sub>2</sub> nanomaterials could be obtained by using surfactants and ligands with long alkyl chains. However, these capped surfactants or ligands on the surface of TiO<sub>2</sub> crystals may cause trapping of electrons in the EEL thus decreasing the PCE.<sup>31</sup>

Herein, we synthesized ligand-free rutile and anatase TiO<sub>2</sub> nanocrystals by using a hydrolytic sol-gel reaction, followed by a phase separation from the bulk solvent by gravity. These two kinds of TiO<sub>2</sub> nanocrystals with high purity are uniform in shape and can be well-dispersed in water. Due to the clean surface and excellent electron extraction property, the device based on anatase TiO<sub>2</sub> shows a significant enhancement in PCE compared with the devices based on rutile and amorphous TiO<sub>2</sub>.

## 2. Experimental section

### 2.1 Materials

TiCl<sub>3</sub> (15.0–20.0% basis in 30% HCl) and ethyl alcohol (98%) were purchased from Aladdin. SnCl<sub>4</sub> (99.9%), titanium isopropoxide (TTIP, 97%), isopropyl alcohol (IPA, 99%), chlorobenzene (99%), and 1,8-diiodooctane (DIO, 98%) were purchased from Alfa Aesar. PTB7 was purchased from 1-Materials Inc. PC<sub>71</sub>BM (99%) was purchased from Solenne BV Inc. All chemicals were used as received without further treatment.

### 2.2 Synthesis of the anatase/rutile TiO<sub>2</sub> nanocrystals

Anatase/rutile TiO<sub>2</sub> nanocrystals were synthesized by using a developed synthetic method with slight modification.<sup>32</sup> (1) Synthesis of rutile nanocrystals: aqueous solutions of TiCl<sub>3</sub> (~20%, 1.6 mL) and SnCl<sub>4</sub> (0.5 M, 1.0 mL) were mixed with ethanol (60 mL) in a glass bottle. After being sealed with parafilm, the reaction mixture was heated at 75 °C in a water bath. After 4 hours, the products precipitated at the bottom of the bottle. (2) Synthesis of anatase nanocrystals: aqueous solutions of TiCl<sub>3</sub> (~20%, 1 mL) and HCl (6 M, 1.0 mL) were mixed with ethanol (60 mL) in a bottle. After being sealed with parafilm, the reaction mixture was heated at 75 °C in a water bath. After 6 h, the products deposited at the bottom of the bottle. Rutile and anatase TiO<sub>2</sub> nanocrystals were collected by pouring out the supernatant ethanol and then washed with ethanol through centrifugation at 8000 rpm for 3 times to remove the Sn<sup>4+</sup> or HCl. The final products were redispersed into the water for device fabrication.

### 2.3 Material characterization

The X-ray diffraction (XRD) patterns were recorded by a Bruker D8 X-ray diffractometer with Cu K $\alpha$  radiation ( $\lambda = 1.5406 \text{ \AA}$ , 40 kV, 40 mA). Transmission electron microscopy (TEM) and high-resolution TEM (HRTEM) images were obtained on a FEI Tecnai G2 F30 transmission electron microscope. X-ray photoelectron

spectroscopy (XPS) and ultraviolet photoelectron spectroscopy (UPS) images were recorded on a Kratos Axis Ultra DLD photoelectron spectrograph. The UV-vis absorption measurements of TiO<sub>2</sub> films deposited onto quartz substrates were measured by a Shimadzu UV-3101 PC spectrophotometer at room temperature. The thickness of the different TiO<sub>2</sub> layers on the ITO glasses was measured by a Hitachi (S-4800) field emission scanning electron microscope (SEM).

### 2.4 Device fabrication

The inverted organic solar cells were fabricated with the structure sequence of ITO/TiO<sub>2</sub> (amorphous TiO<sub>2</sub> or TiO<sub>2</sub> nanocrystals)/PTB7 : PC<sub>71</sub>BM/MoO<sub>3</sub>/Ag. The ITO-coated glass substrates were pre-cleaned with deionized water, acetone, and isopropanol in an ultrasonic bath for 15 min each. Subsequently, a thin layer (approximately 25 nm, Fig. S1, ESI<sup>†</sup>) of rutile or anatase TiO<sub>2</sub> (10 wt%) was spin-coated onto ITO glasses and dried on a hot plate at 130 °C for 30 min. The device based on amorphous TiO<sub>2</sub> as a reference was prepared using a sol-gel method, in which the TiO<sub>2</sub> precursor solution was spin-coated on the ITO-coated glass with a procedure reported previously.<sup>33</sup> Subsequently, the active layer PTB7 : PC<sub>71</sub>BM (1 : 1.5 weight ratio) was spin-coated on the electron extraction layers under N<sub>2</sub> atmosphere from a homogeneous solution of 20 mg mL<sup>-1</sup>. The solution was prepared by dissolving PTB7 and PC<sub>71</sub>BM in chlorobenzene with a 3% volume ratio of 1,8-diiodooctane (DIO) additive. Finally, MoO<sub>3</sub> (10 nm) and Ag (100 nm) were thermally evaporated at a pressure below  $2 \times 10^{-6}$  Torr.

### 2.5 Device characterization

The current density–voltage (*J*–*V*) characteristics were measured using a Keithley 6430 Source Measure Unit. The performance measurements of the OSCs were carried out using an Air Mass 1.5 Global (AM 1.5 G) solar simulator with an irradiation intensity of 100 mW cm<sup>-2</sup> (SAN-EI Electric XEC-301S solar simulator). The incident photon to current efficiency (IPCE) was measured by Zolix Solar Cell Scan 100.

## 3. Results and discussion

The morphology of the as-obtained nanocrystals was investigated by TEM. As shown in Fig. 1(a) and (b), the monodispersed anatase and rutile TiO<sub>2</sub> nanoparticles exhibit an average size of 11.0 nm and 12.4 nm, respectively (insets of Fig. 1(a) and (b)). The HRTEM images demonstrate that these two kinds of TiO<sub>2</sub> nanoparticles are well-crystalline (Fig. 1(c) and (d)). The interplanar distances of the lattice fringes are 0.22 nm and 0.19 nm, corresponding to the (111) planes of the anatase TiO<sub>2</sub> crystal and (200) planes of the rutile TiO<sub>2</sub> crystal.<sup>34,35</sup>

Fig. 2 shows X-ray diffraction patterns of the anatase TiO<sub>2</sub> and rutile TiO<sub>2</sub> nanocrystals. The diffraction peaks for the pure samples can be completely indexed to the anatase phase TiO<sub>2</sub> and rutile phase TiO<sub>2</sub> (JCPDS card file no. 21-1272 and no. 21-1276).<sup>36,37</sup> Both samples possess high purity. The grain size of these two kinds of TiO<sub>2</sub> nanocrystals was determined by the X-ray diffraction using the Scherrer equation:



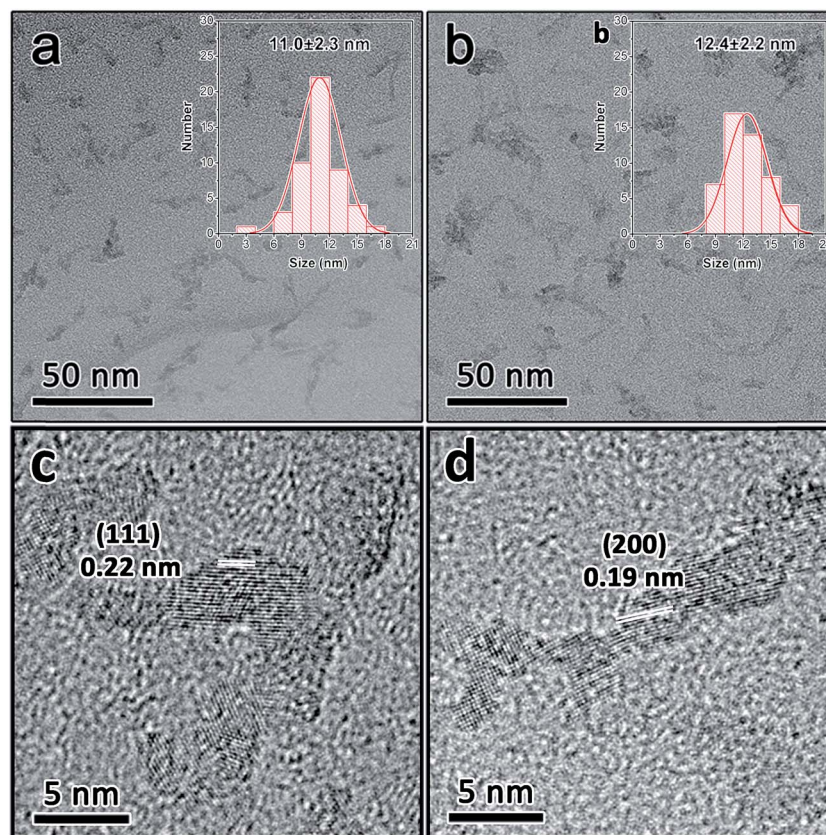


Fig. 1 TEM images of anatase (a) and rutile (b)  $\text{TiO}_2$  nanocrystals. HRTEM image of anatase (c) and rutile (d)  $\text{TiO}_2$  nanocrystals.

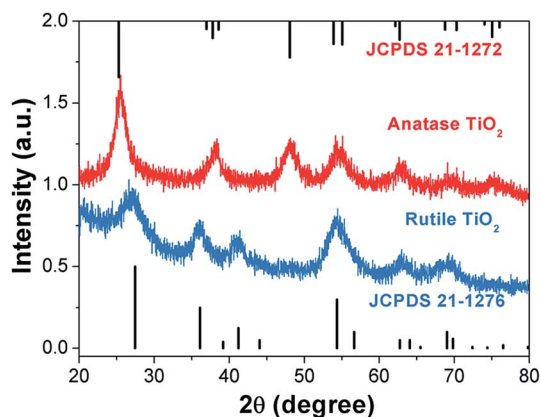


Fig. 2 XRD patterns of anatase and rutile  $\text{TiO}_2$  nanocrystals.

$$D = \left( \frac{k\lambda}{\beta \cos \theta} \right) \quad (1)$$

where  $D$  is the grain size in nanometers,  $\lambda$  is the wavelength of the radiation (1.54056 Å for Cu  $K\alpha$  radiation),  $k$  is a constant equal to 0.94,  $\beta$  is the peak width at half-maximum intensity and  $\theta$  is the peak position.<sup>38,39</sup> The average crystalline grain sizes are  $\sim 4.0$  and  $3.8$  nm for the anatase  $\text{TiO}_2$  and rutile  $\text{TiO}_2$  nanocrystals, respectively. The grain sizes of these two  $\text{TiO}_2$

nanocrystals are smaller than the particle size according to the TEM images, indicating both  $\text{TiO}_2$  nanocrystals are polycrystalline.

To determine the composition and identify the chemical states of the anatase and rutile  $\text{TiO}_2$  nanocrystals, XPS analysis was carried out. Fig. 3 shows Ti 2p and O 1s regions of the high resolution XPS spectra of the anatase and rutile  $\text{TiO}_2$  nanocrystals. The two strong peaks from the anatase and rutile  $\text{TiO}_2$  nanocrystals at around 465.2 eV and 459.5 eV with symmetry can be attributed to Ti 2p<sub>1/2</sub> and Ti 2p<sub>3/2</sub>, respectively (Fig. 3(a) and (c)).<sup>40</sup> The peak positions and 5.8 eV peak separation of the Ti 2p doublet agree well with the energy reported for  $\text{TiO}_2$  nanoparticles.<sup>41,42</sup> Fig. 3(b) and (d) present the O 1s XPS spectra of the above two samples. The peaks of O 1s are located at about 530.8 eV, whose energy is equal to the O 1s electron binding energy for  $\text{TiO}_2$ .<sup>43</sup> Also, there is one more peak in both samples observed at binding energy of 532.0 eV, which was attributed to the H–O from the absorbed  $\text{H}_2\text{O}$  on their surface.<sup>44</sup> Although the atomic ratio of Ti/Sn was about 4 : 1 in the initial reactant, the signal of the  $\text{Sn}^{4+}$  was not detected in the XPS spectrum of the rutile  $\text{TiO}_2$ , which is consistent with previous literature.<sup>32</sup> Fourier-transform infrared spectra (FTIR) of the as-prepared  $\text{TiO}_2$  nanocrystals were measured (Fig. S2, ESI†). These results demonstrate that there is no ligand or surfactant on their surfaces.

The UPS and UV-visible absorption spectra of the anatase and rutile  $\text{TiO}_2$  films are shown in Fig. 4 to study their energy levels. For comparison, a film of amorphous  $\text{TiO}_2$  was prepared



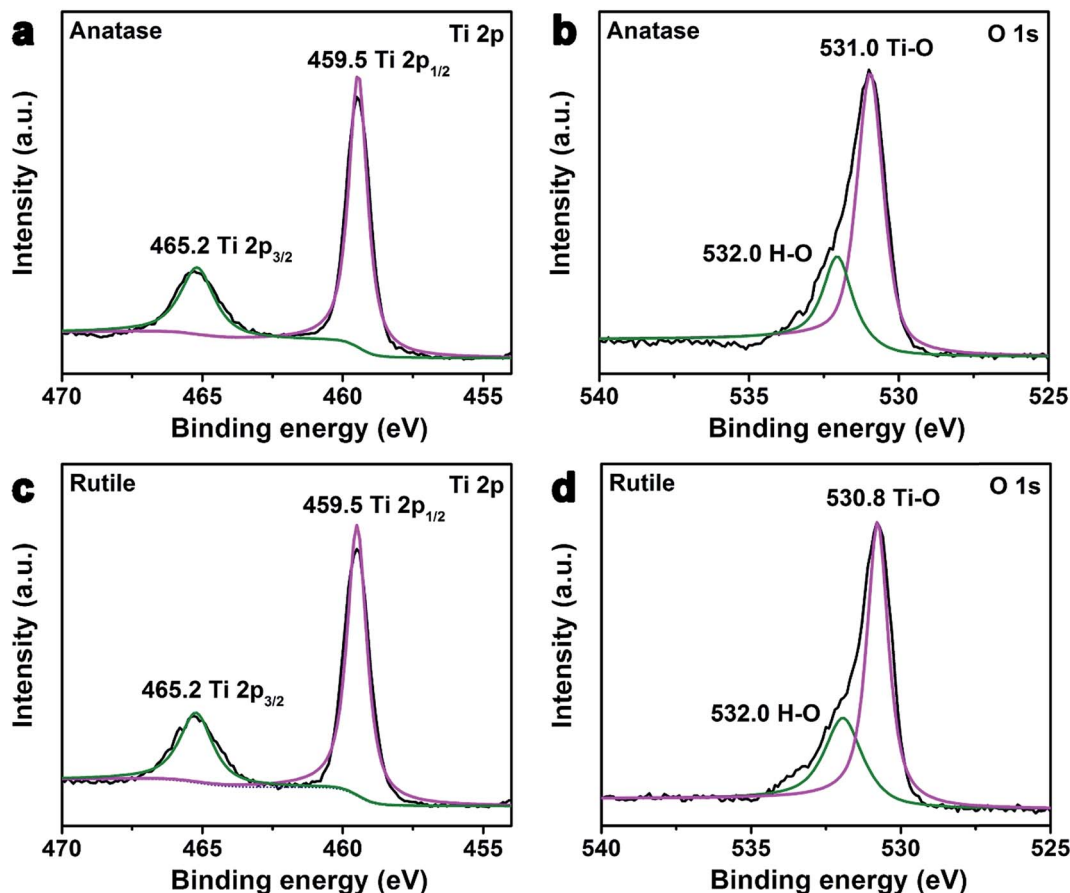


Fig. 3 XPS spectra of anatase and rutile TiO<sub>2</sub> nanocrystals. High resolution Ti 2p spectra for (a) anatase and (c) rutile TiO<sub>2</sub> nanocrystals. High resolution O 1s spectra for (b) anatase and (d) rutile TiO<sub>2</sub> nanocrystals.

as the reference interfacial layer by using a procedure reported previously.<sup>33</sup> The valence band maximum (VBM) level values of the TiO<sub>2</sub> films can be calculated from Fig. 4(a), meanwhile, according to the classical Tauc's formula (eqn (2)) for an indirect band gap semiconductor, the optical band gap ( $E_g$ ) can also be calculated from the Fig. 4(b).<sup>33</sup>

$$(\alpha hv)^{1/2} = A(hv - E_g) \quad (2)$$

where  $\alpha$  is the absorption coefficient,  $hv$  is the incident photon energy and  $A$  is a constant.<sup>45</sup> Thus, the conduction band minimum (CBM) level values of the TiO<sub>2</sub> films could be determined by the VBM and  $E_g$ . All of the above energy level results are summarized in Table 1. The band gap of anatase TiO<sub>2</sub> increased from 3.2 eV (bulk material) to 3.3 eV (nanocrystal), and the band gap of rutile TiO<sub>2</sub> increased from 3.0 eV (bulk material) to 3.2 eV (nanocrystal).<sup>46</sup> These results, which are consistent with previous literature, could be explained by the quantum confinement effect.<sup>47</sup>

The structures of i-OSCs with the amorphous, anatase, and rutile TiO<sub>2</sub> films as the electron extraction layers are shown in Fig. 5(a). The device structure is ITO/TiO<sub>2</sub>/PTB7 : PC<sub>71</sub>BM/MoO<sub>3</sub>/Ag and the energy level diagrams of each component used in the devices are illustrated in Fig. 5(b). Due to the deep

VBM level of these three kinds of TiO<sub>2</sub>, it is reasonable to realize the hole-blocking and thus reduce the loss of the interfacial charge recombination. On the other hand, because their CBM level values are closer to the lowest unoccupied molecular orbital (LUMO) of PC<sub>71</sub>BM, these TiO<sub>2</sub> layers could easily create a quasi-ohmic contact, providing the effective electron transport pathways and enhancing electron extraction.<sup>48</sup>

The current density *versus* voltage ( $J$ - $V$ ) characteristics of i-OSCs with the above three kinds of TiO<sub>2</sub> interfacial layers under AM 1.5 G irradiation (100 mW cm<sup>-2</sup>) are shown in Fig. 6, and the detailed device parameters are summarized in Table 2. Compared with the devices fabricated by amorphous and rutile TiO<sub>2</sub> layers, the optimized solar cell with the anatase TiO<sub>2</sub> layer shows a significant enhancement in the performances: the short-circuit current density ( $J_{sc}$ ) increased from 13.92 mA cm<sup>-2</sup> to 15.66 mA cm<sup>-2</sup>, the open-circuit voltage ( $V_{oc}$ ) from 0.69 V to 0.71 V, the fill factor (FF) from 63.57% to 70.63%, and consequently the PCE from 6.11% to 7.85%.

The external quantum efficiency (EQE) spectra of the above three devices are presented in Fig. 7. When the crystalline TiO<sub>2</sub> films are used as electron extraction layers, the EQE of the device shows an obvious enhancement over a broad wavelength range, indicating that more electrons can be extracted and transported to ITO. Moreover, compared with the device using



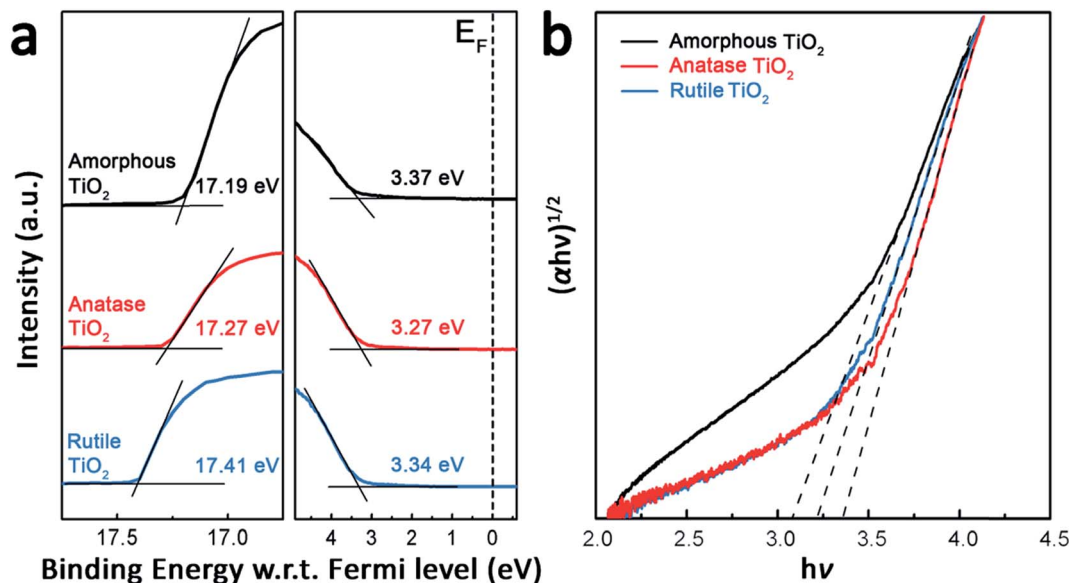


Fig. 4 (a) UPS spectra of various TiO<sub>2</sub> (amorphous, anatase and rutile TiO<sub>2</sub>) films on ITO. (b) The plots of  $(\alpha hv)^{1/2}$  versus photon energy ( $h\nu$ ) for the three types of TiO<sub>2</sub> films prepared on the quartz substrates.

Table 1 Summary of the energy levels for the three electron extraction layers

Electron extraction layer	VBM (eV)	$E_g$ (eV)	CBM (eV)
Amorphous TiO <sub>2</sub>	7.40 ± 0.02	3.07 ± 0.02	4.33 ± 0.02
Anatase TiO <sub>2</sub>	7.22 ± 0.02	3.35 ± 0.02	3.87 ± 0.02
Rutile TiO <sub>2</sub>	7.15 ± 0.02	3.23 ± 0.02	3.92 ± 0.02

the rutile TiO<sub>2</sub> films as interfacial layer, the anatase one shows improved EQE, which demonstrates that the anatase TiO<sub>2</sub> nanocrystals have more effective electron extraction properties than the rutile TiO<sub>2</sub> nanocrystals. Based on the results from the  $J$ - $V$  and EQE spectra, we can conclude that the anatase TiO<sub>2</sub> nanocrystals as electron extraction layer could significantly improve the PCE for the i-OSCs.

In order to further clarify the photovoltaic characteristics, a model based on the single heterojunction solar cell was set up to analyze the  $J$ - $V$  property. According to the equivalent circuit in Fig. 8, the  $J$ - $V$  characteristic could be described by the following equation:<sup>49</sup>

$$J = J_L - J_0 \left[ \exp\left(\frac{e(V + J \times R_s)}{AK_B T}\right) - 1 \right] - \frac{V + J \times R_s}{R_{sh}} \quad (3)$$

where  $J$  is the current density flowing through the external load,  $J_L$  is the light induced constant current density,  $J_0$  is the reverse saturated current density,  $K_B$  is the Boltzmann constant,  $K_B = 1.3806505(24) \times 10^{-23} \text{ J K}^{-1}$ ,  $T$  is the absolute temperature,  $T = 298.15 \text{ K}$ ,  $e$  is the elementary charge,  $e = 1.60217662 \times 10^{-19} \text{ C}$ ,  $R_s$  is the series resistance,  $R_{sh}$  is the shunt resistance,  $A$  is the ideality factor, and  $V$  is the DC bias voltage that is applied to the cell. Some intrinsic parameters of the cell can be derived from

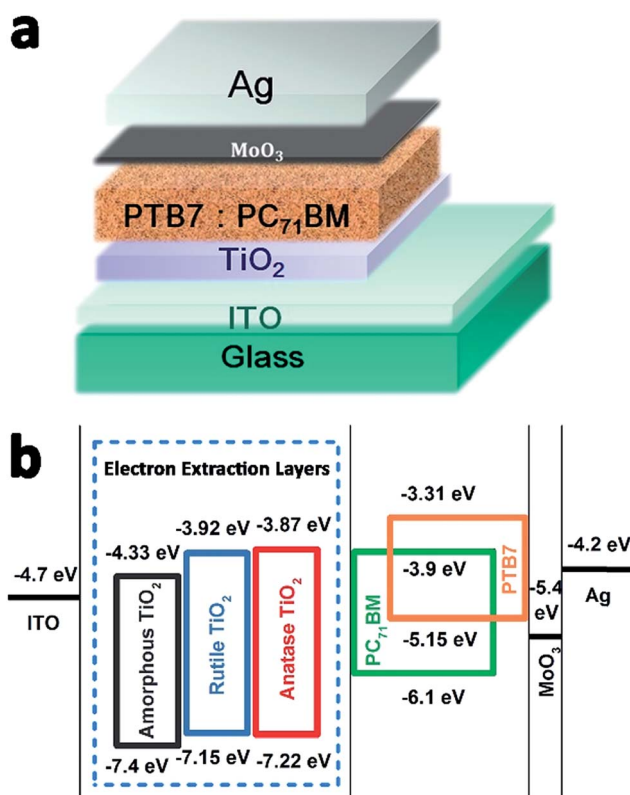


Fig. 5 (a) The structure of the inverted polymer solar cells. (b) Energy level diagram of the component materials used in device fabrication.

eqn (3) for an ideal heterojunction solar cell. Where  $R_{sh}$  is very large, it can be deduced by eqn (4) and (5).

$$\frac{dV}{dJ} = \frac{AK_B T}{e} (J_{sc} - J)^{-1} + R_s \quad (4)$$



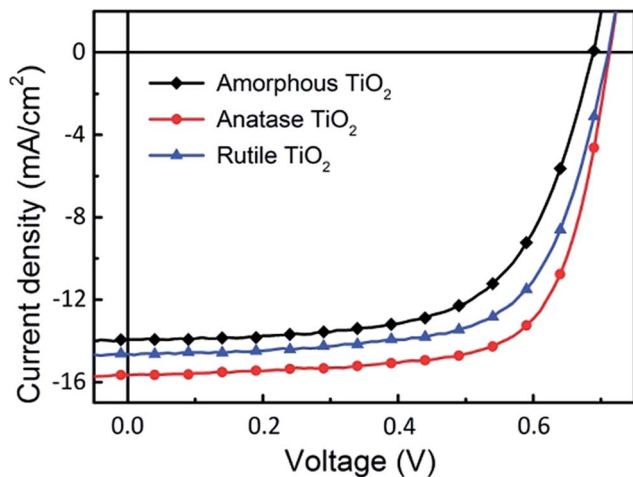


Fig. 6 The  $J$ - $V$  characteristics of the inverted devices using amorphous, anatase and rutile  $\text{TiO}_2$  as electron extraction layers.

Table 2 The current density versus voltage ( $J$ - $V$ ) characteristics of the inverted devices by using amorphous, anatase and rutile  $\text{TiO}_2$  as electron extraction layers

Device	$J_{\text{SC}}$ ( $\text{mA cm}^{-2}$ )	$V_{\text{OC}}$ (V)	FF (%)	PCE (%)
Amorphous $\text{TiO}_2$	13.92	0.69	63.57	6.11
Anatase $\text{TiO}_2$	15.66	0.71	70.63	7.85
Rutile $\text{TiO}_2$	14.64	0.71	66.69	6.93

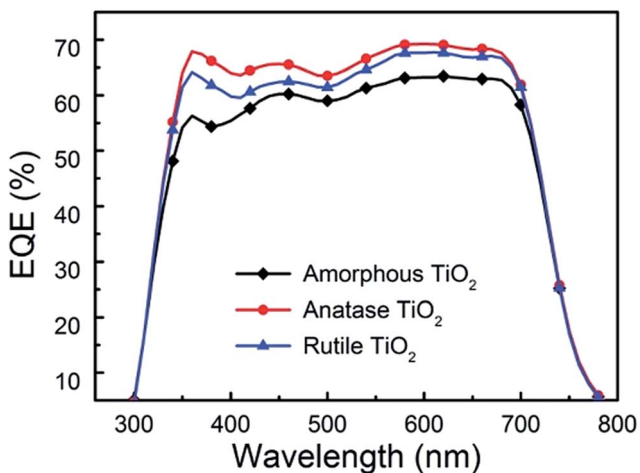


Fig. 7 The IPCE spectra of inverted devices using amorphous, anatase and rutile  $\text{TiO}_2$  as electron extraction layers.

$$\ln(J_{\text{SC}} - J) = \frac{e}{AK_{\text{B}}T}(V + R_{\text{s}} \times J) + \ln J_0 \quad (5)$$

Fig. 9(a), (c) and (e) gives the plots of  $-dV/dJ$  versus  $(J_{\text{SC}} - J)^{-1}$  and the linear fitting curves could be obtained according to eqn (4). It can be found that there is a good linear relationship between  $-dV/dJ$  and  $(J_{\text{SC}} - J)^{-1}$ . The ideality factor  $A$  and series resistance  $R_{\text{s}}$  of the cell are derived from the slope and intercept

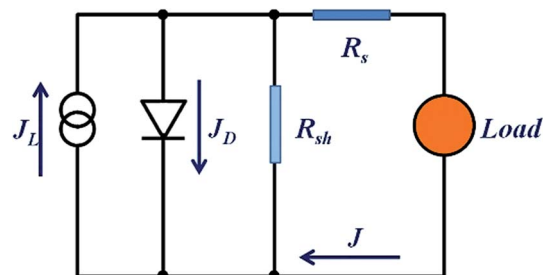


Fig. 8 Single-diode equivalent circuit mode employed in describing the  $J$ - $V$  behavior of the OPVs.

of the linear fitting results, as shown in Table 3. Under illumination, the ideality factors are 2.08 for amorphous  $\text{TiO}_2$ , 1.88 for rutile  $\text{TiO}_2$  and 1.69 for anatase  $\text{TiO}_2$ , respectively. And the series resistances are  $2.32 \Omega \text{ cm}^2$  for amorphous  $\text{TiO}_2$ ,  $2.18 \Omega \text{ cm}^2$  for rutile  $\text{TiO}_2$  and  $1.45 \Omega \text{ cm}^2$  for anatase  $\text{TiO}_2$ .

As we know, a small series resistance is necessary for a high-performance solar cell with a high fill factor according to eqn (3). Therefore, the device based on anatase  $\text{TiO}_2$  shows the best performance among these three devices. The value of the ideality factor represents the quality of a junction and the carrier recombination mechanism in a heterojunction solar cell. For a well-behaved heterojunction solar cell, the ideality factor is typically in the range  $1.3 < A < 2$ . When the diode current of a PN junction is dominated by the carrier diffusion in the neutral region of semiconductors,  $A$  is approaching 1. On the other hand, when carrier recombination in the depleted space-charge region dominates the diode current,  $A$  is approaching 2. For most cases, both carrier diffusion and recombination happened simultaneously, with  $A$  having a corresponding value in the range  $1 < A < 2$ . For the cells based on  $\text{TiO}_2$  nanocrystals,  $A$  is between the ideal regions, which indicates that the cells agree well with the heterojunction solar cell model. For the cell based on amorphous  $\text{TiO}_2$ , the ideality factor is larger than 2, which means that there are additional recombination mechanisms besides the recombination in the charge neutral region and space charge region.<sup>49</sup> The higher values of  $A$  and  $R_{\text{s}}$  from the device employing rutile  $\text{TiO}_2$  compared to the device based on anatase  $\text{TiO}_2$  illuminates that a higher level charge recombination occurs and leads to the poor fill factor and short circuit current.

Fig. 9(b), (d) and (f) gives the plots of  $\ln(J_{\text{SC}} - J)$  versus  $V + R_{\text{s}}J$  and there is also a linear relationship between them. The reverse saturated current density of the cells is  $2.95 \times 10^{-5} \text{ mA cm}^{-2}$  for amorphous  $\text{TiO}_2$ ,  $3.89 \times 10^{-6} \text{ mA cm}^{-2}$  for rutile  $\text{TiO}_2$  and  $1.08 \times 10^{-6} \text{ mA cm}^{-2}$  for anatase  $\text{TiO}_2$ . According to eqn (3), when  $R_{\text{sh}}$  is large enough, the  $V_{\text{OC}}$  of a heterojunction solar cell can be deduced as:

$$V_{\text{OC}} = \frac{AK_{\text{B}}T}{e} \ln\left(\frac{J_{\text{L}} + J_0}{J_0}\right) \approx \frac{AK_{\text{B}}T}{e} \ln\left(\frac{J_{\text{SC}}}{J_0}\right) \quad (6)$$

It is obvious that the  $V_{\text{OC}}$  is determined by the ideality factor, working temperature, light-induced current, and the reverse saturated current of the cell. A low  $J_0$  together with a large



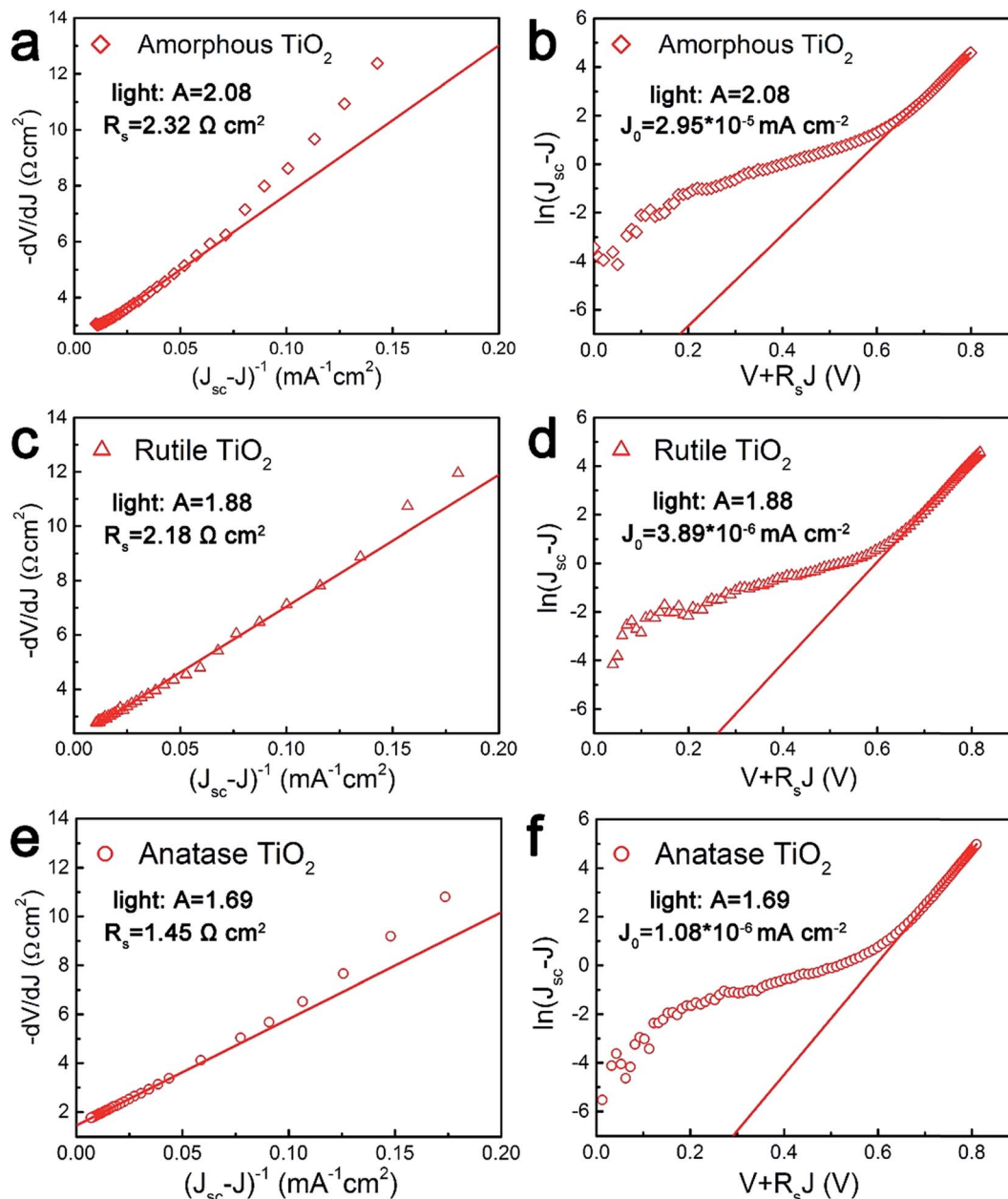


Fig. 9 Plots of  $-dV/dJ$  vs.  $(J_{sc} - J)^{-1}$  and the linear fitting curves (a), (c) and (e), plots of  $\ln(J_{sc} - J)$  against  $V + R_s J$  and the linear fitting curves (b), (d) and (f) from the devices fabricated by using amorphous, rutile and anatase  $\text{TiO}_2$  as electron extraction layers.

**Table 3** Summary of extracted parameters fitted by the plots of  $-dV/dJ$  vs.  $(J_{sc} - J)^{-1}$  and the plots of  $\ln(J_{sc} - J)$  against  $V + R_s J$  from the devices prepared by using amorphous, anatase and rutile  $\text{TiO}_2$  as electron extraction layers

Device	$A$	$R_s$ ( $\Omega \text{ cm}^2$ )	$J_0$ ( $\text{mA cm}^{-2}$ )
Amorphous $\text{TiO}_2$	2.08	2.32	$2.95 \times 10^{-5}$
Anatase $\text{TiO}_2$	1.69	1.45	$1.08 \times 10^{-6}$
Rutile $\text{TiO}_2$	1.88	2.18	$3.89 \times 10^{-6}$

ideality factor are key factors for a high  $V_{OC}$ . For the devices based on the rutile and anatase  $\text{TiO}_2$ , the values of ideality factor and the reverse saturated current are close, which results

in the same  $V_{OC}$ . For the device based on the amorphous  $\text{TiO}_2$ , the reverse saturated current is of the order of  $10^{-5}$  magnitude. But as  $A$  and  $J_0$  have opposite effects on  $V_{OC}$  as shown in eqn (6), this result indicates that  $J_0$  plays a bigger role in changing  $V_{OC}$ . So the larger  $J_0$  of the device based on amorphous  $\text{TiO}_2$  causes the open-circuit voltage to decrease. Similar results have been observed in previous studies.<sup>50,51</sup>

In order to investigate the recombination kinetics of the devices, the open-circuit photovoltage decay (OCVD) measurements were conducted. OCVD has been widely used to study recombination in DSSCs and perovskite solar cells.<sup>52,53</sup> The cells are illuminated at open circuit to establish a photo stationary state. The light is then switched off, and



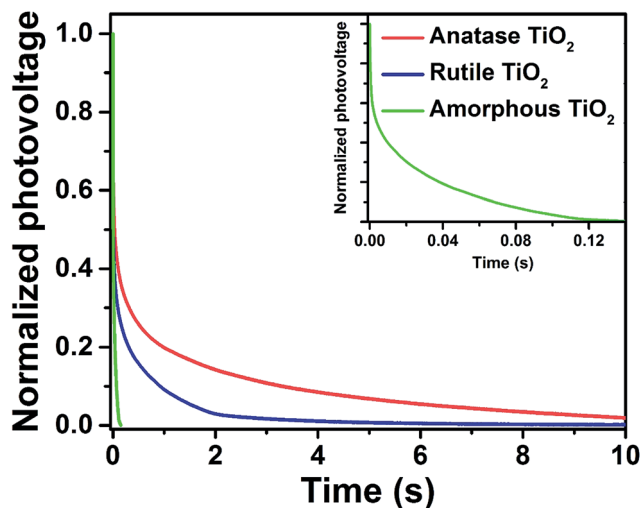


Fig. 10 Open-circuit voltage decays for the three types of TiO<sub>2</sub> based OSCs.

the decay in  $V_{OC}$  is monitored as a function of time. Zaban *et al.* proposed that the rate of photovoltage decay is inversely proportional to the lifetime of the photoelectron in the DSSCs, and that the lifetime of the electron is inversely proportional to the rate of recombination.<sup>52</sup> Experimental OCVD decay plots for the above three devices are shown in Fig. 10. The open-circuit voltage of the cell based on amorphous TiO<sub>2</sub> decays rapidly, falling below 0.1 V within 100 ms. By contrast, the devices based on the crystalline TiO<sub>2</sub> nanocrystals, especially for anatase TiO<sub>2</sub>, exhibited a remarkably slow decay of  $V_{OC}$ , indicating their superior recombination characteristics.

## 4. Conclusion

In summary, we synthesized ligand-free rutile and anatase TiO<sub>2</sub> nanocrystals by using a simple hydrolytic sol-gel reaction. The monodispersed anatase and rutile TiO<sub>2</sub> nanocrystals with high purity exhibited a branched structure. Moreover, we demonstrated that the use of anatase TiO<sub>2</sub> nanocrystals as an electron extraction layer for i-OSCs dramatically improves the devices' power conversion efficiency. Meanwhile, the ideal model for a single heterojunction solar cell has been applied to clarify the cell characteristics. Analysis from the diode parameters shows that anatase TiO<sub>2</sub> nanocrystals could reduce the carrier recombination and improve the performance. It is expected that the ligand-free anatase TiO<sub>2</sub> nanocrystals may have other promising applications in energy-related fields.

## Acknowledgements

This work was supported by National Natural Science Foundation of China (No. 61377028, 61475014, 61475017, 61674012, 61675018), The Fundamental Research Funds for the Central Universities (2014JBZ009).

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